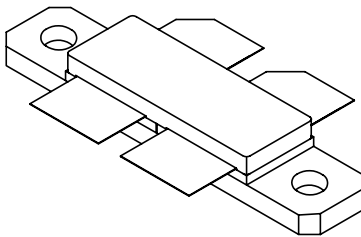
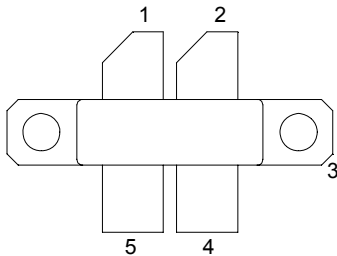


## RF power LDMOS transistor for frequencies up to 1.5 GHz


**M246**

 1-2 Drain  
 4-5 Gate

3 Source

### Features

| Order code | F <sub>REQ</sub> | V <sub>DD</sub> | P <sub>OUT</sub> (typ.) | Gain  | N <sub>D</sub> |
|------------|------------------|-----------------|-------------------------|-------|----------------|
| ST50V10200 | 1000 MHz         | 50 V            | 200 W                   | 18 dB | 60%            |

- High efficiency and linear gain operations
- Integrated ESD protection
- Large positive and negative gate/source voltage range
- In compliance with the European Directive 2002/95/EC

### Applications

- Broadband communications
- Industrial, scientific and medical (ISM)
- Avionics

### Description

The ST50V10200 is a common-source N-channel enhancement-mode lateral field-effect RF power transistor designed for broadband commercial, avionics and industrial applications at frequencies up to 1.5 GHz. It can be used in A/AB and C classes for all typical modulation formats.



#### Product status link

[ST50V10200](#)

#### Product summary

|                   |               |
|-------------------|---------------|
| <b>Order code</b> | ST50V10200    |
| <b>Marking</b>    | ST50V10200 ES |
| <b>Package</b>    | M246          |
| <b>Packing</b>    | TBD           |

# 1 Electrical ratings

**Table 1. Absolute maximum ratings (+25 °C)**

| Symbol     | Parameter                 | Value       | Unit |
|------------|---------------------------|-------------|------|
| $B_{VDSS}$ | Drain-source voltage      | 110         | V    |
| $V_{GS}$   | Gate-source voltage       | -8/+10      | V    |
| $V_{DD}$   | Drain supply voltage      | 18          | V    |
| $T_{STG}$  | Storage temperature range | -65 to +150 | °C   |
| $T_J$      | Junction temperature      | +200        | °C   |

**Table 2. Thermal data**

| Symbol         | Parameter   | Value | Unit |
|----------------|---|-------|------|
| $R_{thj-case}$ | Junction-case thermal resistance<br>$T_{CASE} = +85\text{ °C}$ , $T_J = +200\text{ °C}$ , DC test | 0.40  | °C/W |

**Table 3. ESD protection**

| Symbol | Parameter                                   | Class |
|--------|---|-------|
| HBM    | Human body model (according to JESD22-A114) | 2     |

## 2 Electrical characteristics

( $T_C = 25\text{ }^\circ\text{C}$  unless otherwise specified)

**Table 4. Static (per side)**

| Symbol        | Parameter                          | Test conditions  | Min. | Typ. | Max. | Unit          |
|---------------|------------------------------------|--|------|------|------|---------------|
| $V_{(BR)DSS}$ | Drain-source breakdown voltage     | $V_{GS} = 0\text{ V}$ , $I_D = 100\text{ }\mu\text{A}$                       | 110  |      |      | V             |
| $I_{DSS}$     | Zero-gate voltage drain current    | $V_{GS} = 0\text{ V}$ , $V_{DS} = 50\text{ V}$                               |      |      | 1    | $\mu\text{A}$ |
| $I_{GSS}$     | Gate-body leakage current          | $V_{DS} = 0\text{ V}$ , $V_{GS} = 6\text{ V}$                                |      |      | 1    | $\mu\text{A}$ |
| $V_{GS(th)}$  | Gate threshold voltage             | $V_{DS} = 28\text{ V}$ , $I_D = 600\text{ }\mu\text{A}$                      | 1    | TBD  | 3    | V             |
| $V_{DS(on)}$  | Static drain-source on-resistance  | $V_{GS} = 10\text{ V}$ , $I_D = 5\text{ A}$                                  |      |      | 1.4  | V             |
| $C_{ISS}$     | Common source input capacitance    | $V_{GS} = 0\text{ V}$ , $V_{DD} = 50\text{ V}$ ,<br>$F_{REQ} = 1\text{ MHz}$ |      | 118  |      | pF            |
| $C_{RSS}$     | Common source feedback capacitance |  |      | 2    |      | pF            |
| $C_{OSS}$     | Common source output capacitance   |  |      | 44   |      | pF            |

**Table 5. Dynamic**

| Symbol     | Parameter                 | Test conditions   | Min. | Typ. | Max. | Unit |
|------------|---------------------------|---|------|------|------|------|
| $P_{OUT}$  | Output power              | $V_{DD} = 50\text{ V}$ , $I_{DQ} = 0.2\text{ A}$ ,<br>$F_{REQ} = 1000\text{ MHz}$ , | -    | 225  | -    | W    |
| Gain       | Power gain                |   | -    | 17.5 | -    | dB   |
| Efficiency | Drain efficiency          |   | -    | 60   | -    | %    |
| IMD3       | 3rd order intermodulation |   | -    | TBD  | -    | dBc  |
| VSWR       | Load mismatch             | $P_{OUT} = 200\text{ W}$ , all phases   | -    | 10:1 | -    |      |

**Table 6. Impedance data**

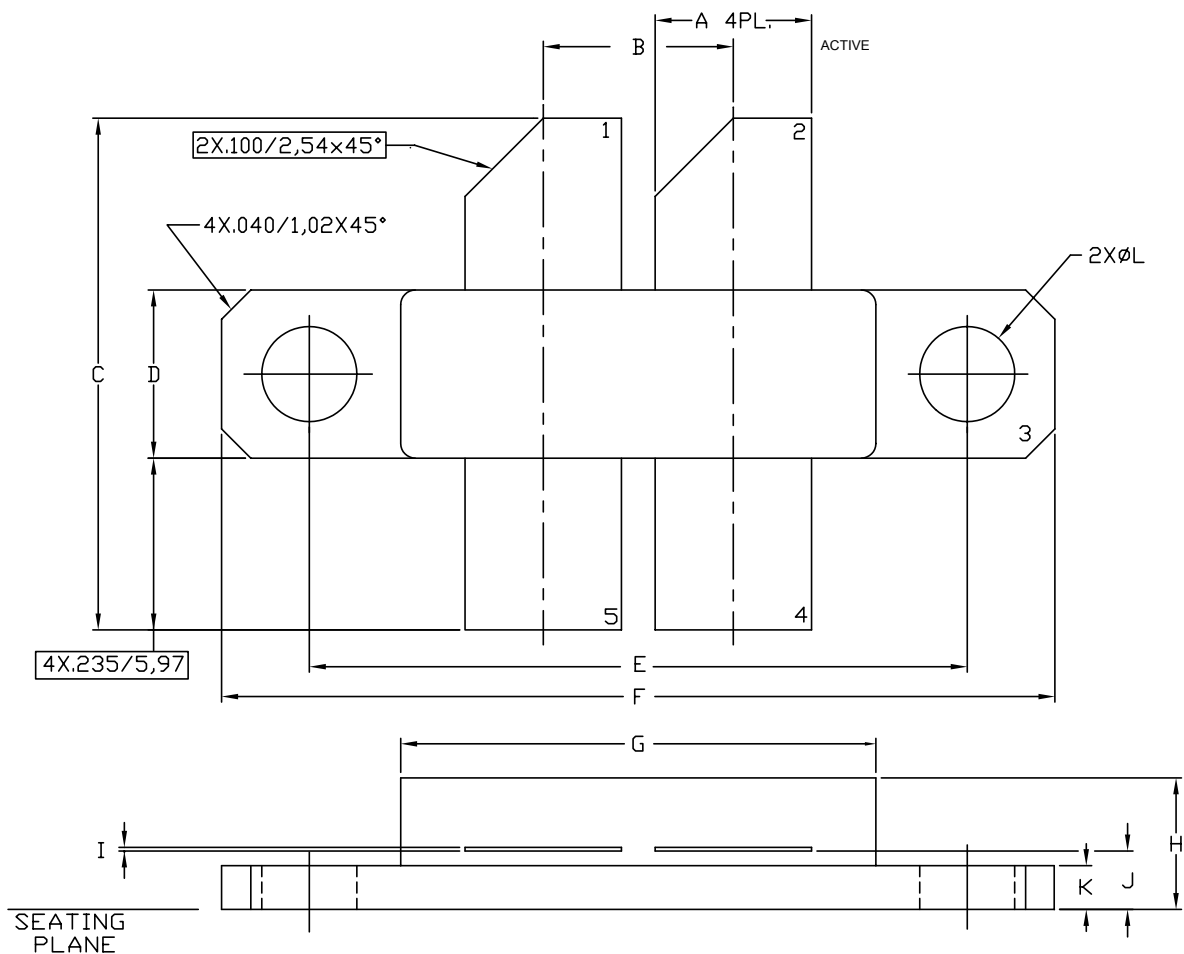
| Frequency (in MHz) | Input impedance ( $Z_{IN}$ ) | Drain load impedance ( $Z_{DL}$ ) |
|--------------------|------------------------------|-----------------------------------|
| 2                  | TBD                          | TBD                               |
| 5                  | TBD                          | TBD                               |
| 10                 | TBD                          | TBD                               |
| 30                 | TBD                          | TBD                               |
| 60                 | TBD                          | TBD                               |
| 100                | TBD                          | TBD                               |
| 200                | TBD                          | TBD                               |

### 3 Package information

In order to meet environmental requirements, ST offers these devices in different grades of **ECOPACK** packages, depending on their level of environmental compliance. ECOPACK specifications, grade definitions and product status are available at: [www.st.com](http://www.st.com). ECOPACK is an ST trademark.

#### 3.1 0.230 x 0.650 WIDE 4/L BAL N/HERM W/FLG M246 package information

**Figure 1. 0.230 x 0.650 WIDE 4/L BAL N/HERM W/FLG M246 package outline**



7145054\_5

**Table 7. 0.230 x 0.650 WIDE 4/L BAL N/HERM W/FLG M246 mechanical data**

| Symbol | Millimeters |       |       |
|--------|-------------|-------|-------|
|        | Min.        | Typ.  | Max.  |
| A      | 5.33        |       | 5.59  |
| B      | 6.48        |       | 6.73  |
| C      | 17.27       |       | 18.29 |
| D      | 5.72        |       | 5.97  |
| E      |             | 22.86 |       |
| F      | 28.83       |       | 29.08 |
| G      | 16.26       |       | 16.76 |
| H      | 4.19        |       | 5.08  |
| I      | 0.08        |       | 0.15  |
| J      | 1.83        |       | 2.24  |
| K      | 1.40        |       | 1.65  |
| L      | 3.18        |       | 3.43  |

## Revision history

**Table 8. Document revision history**

| Date        | Version | Changes   |
|-------------|---------|---|
| 12-Sep-2018 | 1       | Initial release   |
| 22-Mar-2019 | 2       | Updated <a href="#">Table 1</a> and <a href="#">Table 4</a> . |

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